

2881

PATENT  
81880.0087

FORM PTO-1083



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Hirovuki HOSHITA et al.

Serial No: 08/808,315

Filed: February 28, 1997

For: SAPPHIRE SINGLE CRYSTAL,  
SEMICONDUCTOR LASER DIODE USING THE  
SAME FOR SUBSTRATE, AND METHOD FOR  
MANUFACTURING THE SAME (As Amended)

Art Unit: 2881

Examiner: J. Menefee

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents Washington D.C. 20231, on February 8, 2001

Date of Deposit

Kathleen J. Dunn

Name

Signature

February 8, 2001  
Date

Box NON-FEE AMENDMENT

Commissioner for Patents

Washington, D.C. 20231

Dear Sir:

Transmitted herewith is an amendment in the above-identified application.

- ☐ Small entity status of this application under 37 C.F.R. 1.9 and 1.27 has been established by a verified statement previously submitted.
- ☐ A verified statement to establish small entity status under 37 C.F.R. 1.9 and 1.27 is enclosed.
- ☐ A Notice Of Change Of Attorney's Address and Associate Power Of Attorney is enclosed.
- ☒ No additional fee is required.

The fee has been calculated as shown below:

the fee has been calculated as shown below.

	(Col. 1) CLAIMS REMAINING AFTER AMENDMENT		(Col. 2) HIGHEST NUMBER PREVIOUSLY PAID FOR	(Col. 3) PRESENT EXTRA*	LG/SM \$ ENTITY FEE		ADD'L FEE DUE
TOTAL CLAIMS FEE	3	-	20**	0	LG=\$18 SM=\$9	\$0	\$ 0
INDEPENDENT CLAIMS FEE	2	-	3***	0	LG=\$80 SM=\$40	\$0	\$ 0
FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIMS					LARGE ENTITY FEE = \$270 SMALL ENTITY FEE = \$135		\$ 0
TOTAL							\$ 0

\* If the entry in Col. 1 is less than the entry in Col. 2, write "0" in Col. 3.

\*\* If the "Highest Number Previously Paid For" IN THIS SPACE is less than 20, write "20" in this space.

\*\*\* If the "Highest Number Previously Paid For" IN THIS SPACE is less than 3, write "3" in this space. The "Highest Number Previously Paid For" (Total or Independent) is the highest number found from the equivalent box on Col. 1 of a prior amendment or the number of claims originally filed.

- ☐ A check in the amount of \$\_\_\_ to cover the additional claims fee is enclosed. **A copy of this sheet is enclosed.**
- ☐ A check in the amount of \$\_\_\_ to cover the extension fee is enclosed. **A copy of this sheet is enclosed.**
- ☒ The Commissioner is hereby authorized to charge any deficiencies of fees associated with this communication or credit any overpayment to Deposit Account No. 50-1314. **A copy of this sheet is enclosed.**
- ☒ Any filing fees under 37 C.F.R. 1.16 for the presentation of extra claims
- ☒ Any patent application processing fees under 37 C.F.R. 1.17

Respectfully submitted,  
HOGAN & HARTSON L.L.P.

By:

Stefan J. Kirchanski

Stefan J. Kirchanski

Registration No. 36,568

Attorney for Applicant(s)

Date: February 8, 2001

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PATENT  
Docket No. 81880.0087  
(Former Docket No. 247PD-5385)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Hiroyuki KINOSHITA et al.

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Kathleen J. Dunn

Name

*Kathleen J. Dunn*

Signature

Date

**AMENDMENT**

Box Non-Fee Amendment  
Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

In response to the Office Action dated November 13, 2000, please amend  
the above-identified application as follows:

**IN THE SPECIFICATION:**

Please delete the Abstract and replace it with the following text:

E1  
The present invention relates to a sapphire monocrystalline body to be  
used as the substrate for a semiconductor for electronic parts or component parts,  
and to a monocrystalline sapphire substrate. The invention also relates to a  
method for working the same. The invention is based cleavage along the plane R  
of the sapphire monocrystalline body which cleavage is easy to accomplish and  
provides a surface high in precision. The inventive process includes forming  
linear crack parallel or vertical to a reference plane of the substrate, with a